



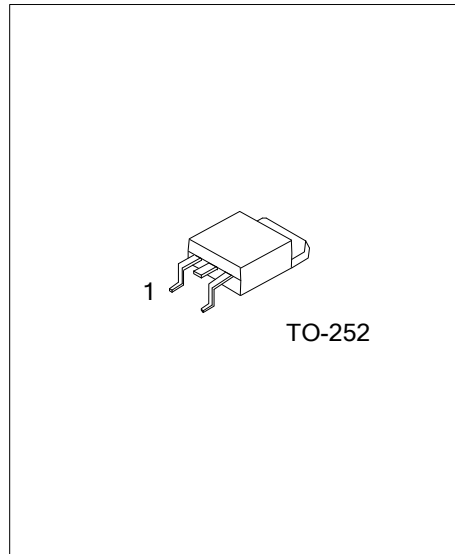
HJ45H11

PNP SILICON TRANSISTOR

PNP EPITAXIAL PLANAR TRANSISTOR

DESCRIPTION

The HJ45H11 is designed for various specific and general purpose applications, such as: output and driver stages of amplifiers operating at frequencies from DC to greater than 1MHz; series, shunt and switching regulators; low and high frequency inverters/converters; and many others.



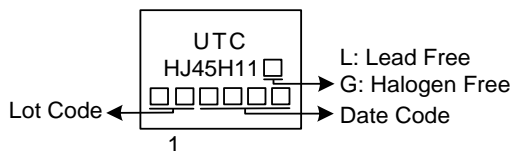
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
HJ45H11L-TN3-R	HJ45H11G-TN3-R	TO-252	B	C	E	Tape Reel

Note: Pin Assignment: B: Base C: Case E: Emitter

<p>HJ45H11G-TN3-R</p> <p>(1) Packing Type (2) Package Type (3) Green Package</p>	<p>(1) R: Tape Reel (2) TN3: TO-252 (3) G: Halogen Free and Lead Free, L: Lead Free</p>
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MARKING



■ **ABSOLUTE MAXIMUM RATINGS** ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector- Emitter Voltage	V_{CEO}	-80	V
Collector-Emitter Voltage	V_{CES}	-80	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-10	A
Base Current	I_B	-5	A
Power Dissipation ($T_C=25^{\circ}\text{C}$)	P_D	20	W
Junction Temperature	T_J	+150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

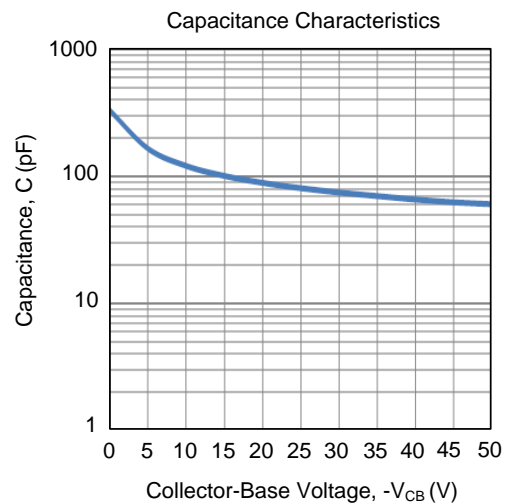
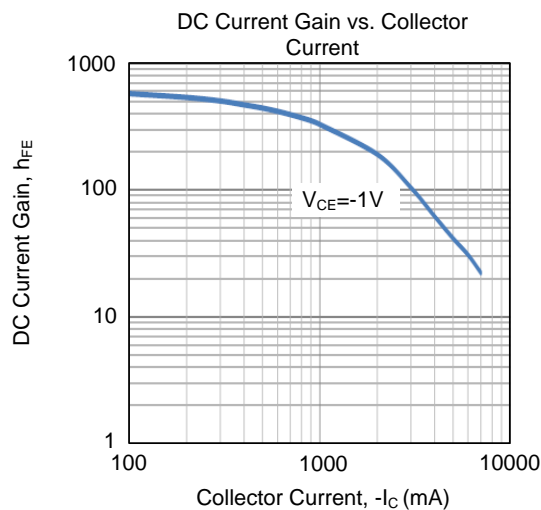
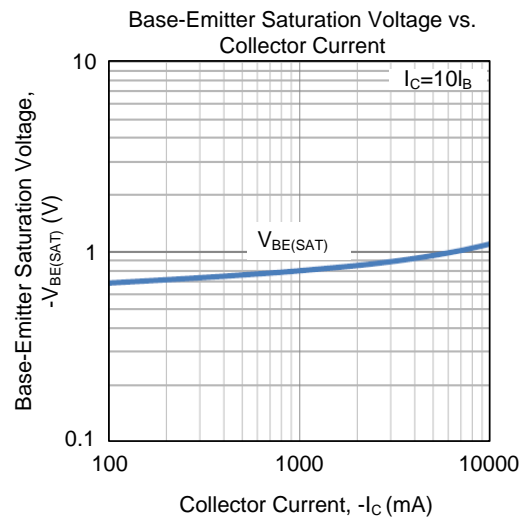
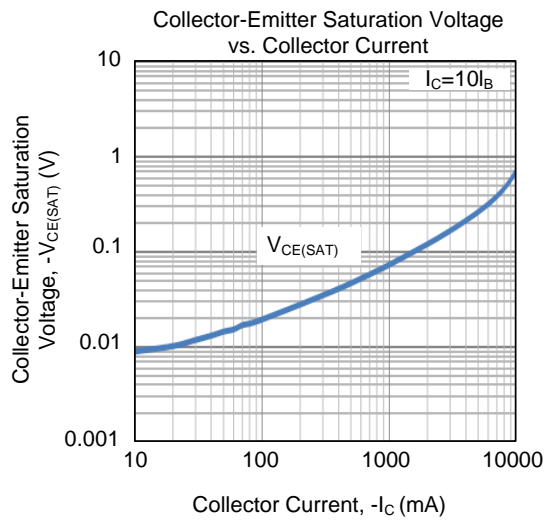
Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ **ELECTRICAL CHARACTERISTICS** ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=-30\text{mA}$, $I_B=0$	-80			V
Collector-Emitter Breakdown Voltage	BV_{CES}	$I_C=-1\text{mA}$, $I_B=0$	-80			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=-1\text{mA}$, $I_C=0$	-5			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-80\text{V}$, $V_{EB}=0$			-10	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=-5\text{V}$, $I_C=0$			-50	μA
Collector-Emitter Saturation Voltage(Note)	$V_{CE(SAT)}$	$I_C=-8\text{A}$, $I_B=-0.8\text{A}$			-1	V
Base-Emitter Saturation Voltage(Note)	$V_{BE(SAT)}$	$I_C=-8\text{A}$, $I_B=-0.8\text{A}$			-1.5	V
DC Current Gain (Note)	h_{FE1}	$V_{CE}=-1\text{V}$, $I_C=-2\text{A}$	60			
	h_{FE2}	$V_{CE}=-1\text{V}$, $I_C=-4\text{A}$	40			
Output Capacitance	C_{OB}	$V_{CB}=-10\text{V}$		120		pF

Note: Pulse Test: Pulse Width $\leq 380\mu\text{s}$, Duty Cycle $\leq 2\%$.

■ TYPICAL CHARACTERISTICS



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